

BFQ591

NPN 7 GHz wideband transistor

Rev. 04 — 2 October 2007

Product data sheet

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NXP Semiconductors

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BFQ591

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

Intended for applications in the GHz range such as MATV or CATV amplifiers and RF communications subscribers equipment.

DESCRIPTION

NPN wideband transistor in a SOT89 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BFQ591	BCp

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base

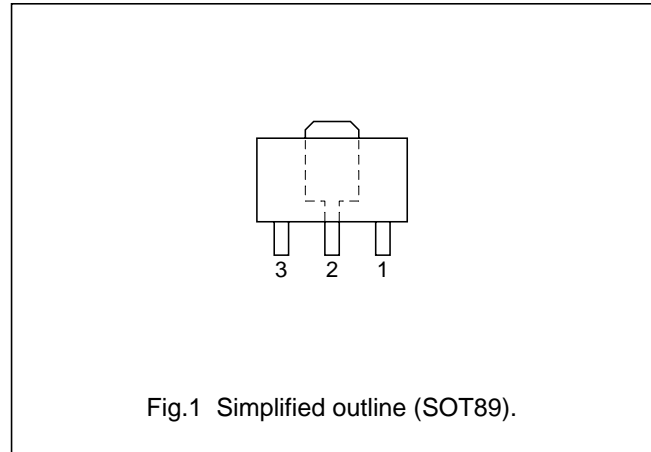


Fig.1 Simplified outline (SOT89).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CB0}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	collector current (DC)		–	–	200	mA
P_{tot}	total power dissipation	$T_s \leq 90\text{ }^\circ\text{C}$; note 1	–	–	2.25	W
h_{FE}	DC current gain	$I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$	60	90	250	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 12\text{ V}$; $f = 1\text{ MHz}$	–	0.8	–	pF
f_T	transition frequency	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 1\text{ GHz}$	–	7	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	11	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	10	–	dB

Note

1. T_s is the temperature at the soldering point of the collector pin.

NPN 7 GHz wideband transistor

BFQ591

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	20	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	collector current (DC)		–	200	mA
P _{tot}	total power dissipation	T _s ≤ 90 °C; note 1	–	2.25	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	175	°C

Note

1. T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	T _s ≤ 90 °C; note 1	38	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

NPN 7 GHz wideband transistor

BFQ591

CHARACTERISTICS

$T_j = 25\text{ °C}$; unless otherwise specified.

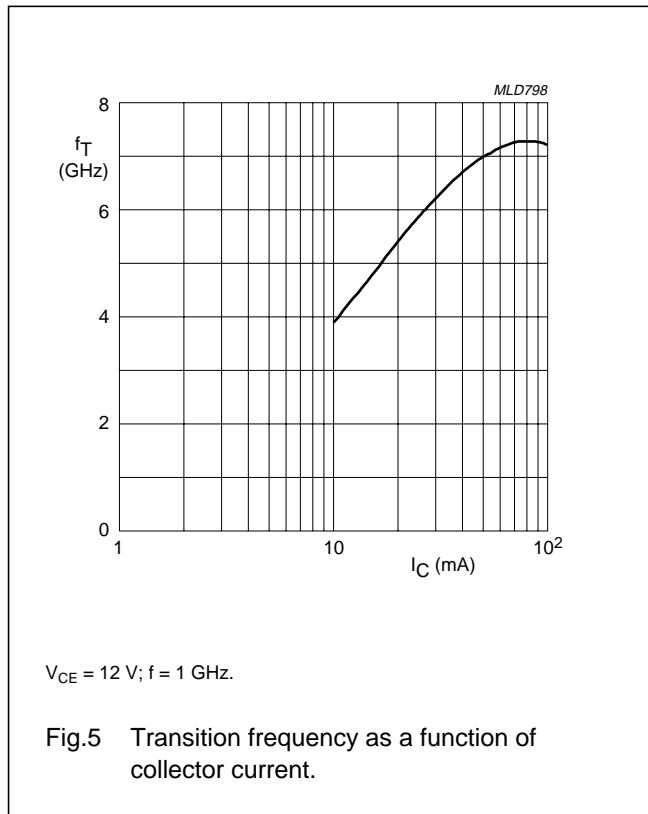
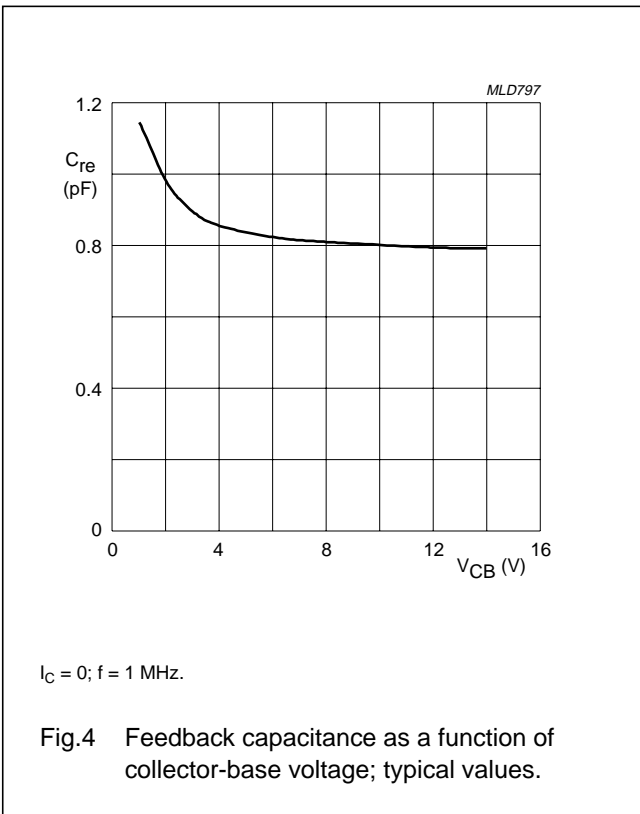
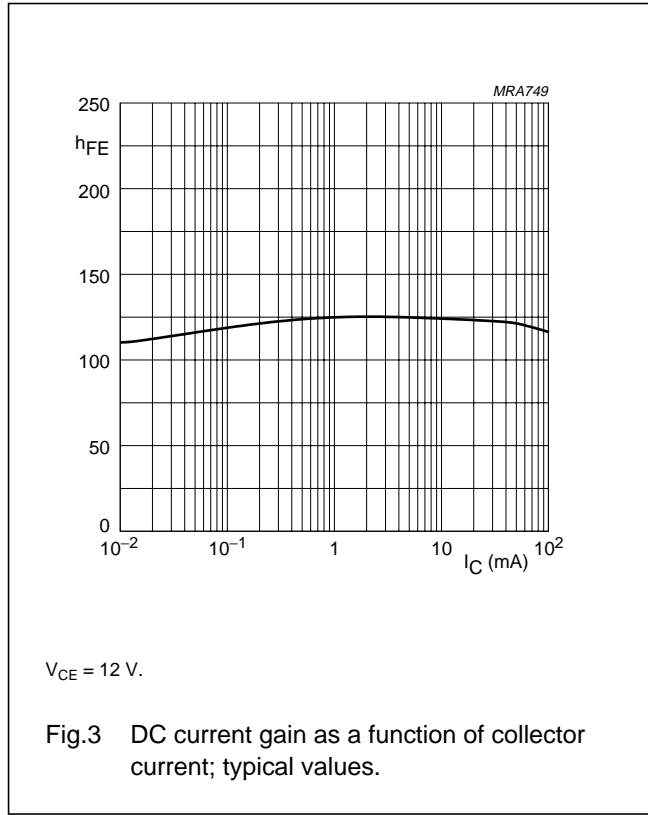
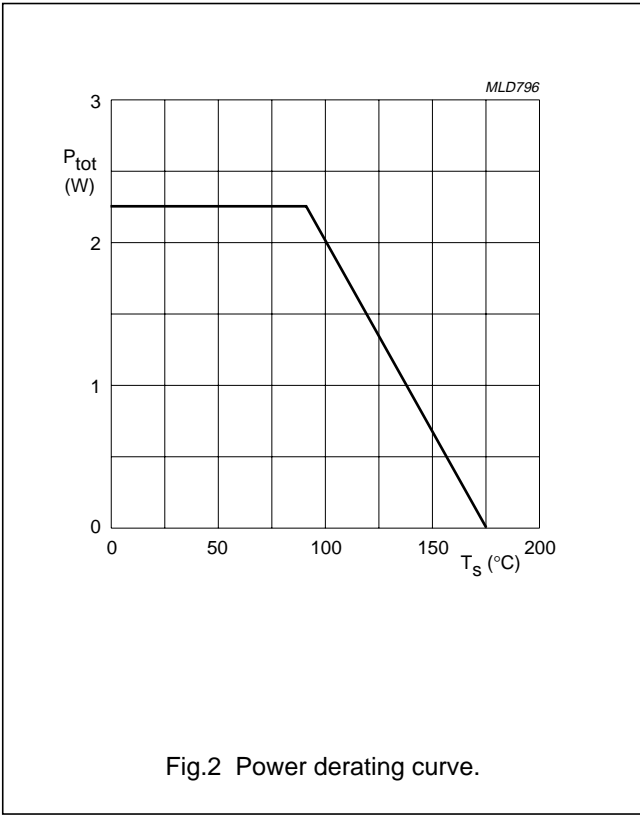
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 0.1\text{ mA}$; $I_E = 0$	–	–	20	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 0.1\text{ mA}$; $I_B = 0$	–	–	15	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 0.1\text{ mA}$; $I_C = 0$	–	–	3	V
I_{CBO}	collector-base leakage current	$I_E = 0$; $V_{CB} = 10$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$	60	90	250	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 12\text{ V}$; $f = 1\text{ MHz}$	–	0.8	–	pF
f_T	transition frequency	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 1\text{ GHz}$	–	7	–	GHz
G_{UM}	maximum unilateral power gain; note 1	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $T_{amb} = 25\text{ °C}$ $f = 900\text{ MHz}$ $f = 2\text{ GHz}$	–	11 5.5	–	dB dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	10	–	dB
V_o	output voltage	note 2	–	700	–	mV

Notes

- G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero and $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB.
- $d_{im} = 60\text{ dB}$ (DIN45004B); $V_p = V_o$; $V_q = V_o - 6\text{ dB}$; $f_p = 795.25\text{ MHz}$; $f_q = 803.25\text{ MHz}$; $f_r = 803.25\text{ MHz}$;
measured at $f_{(p+q+r)} = 793.25\text{ MHz}$.

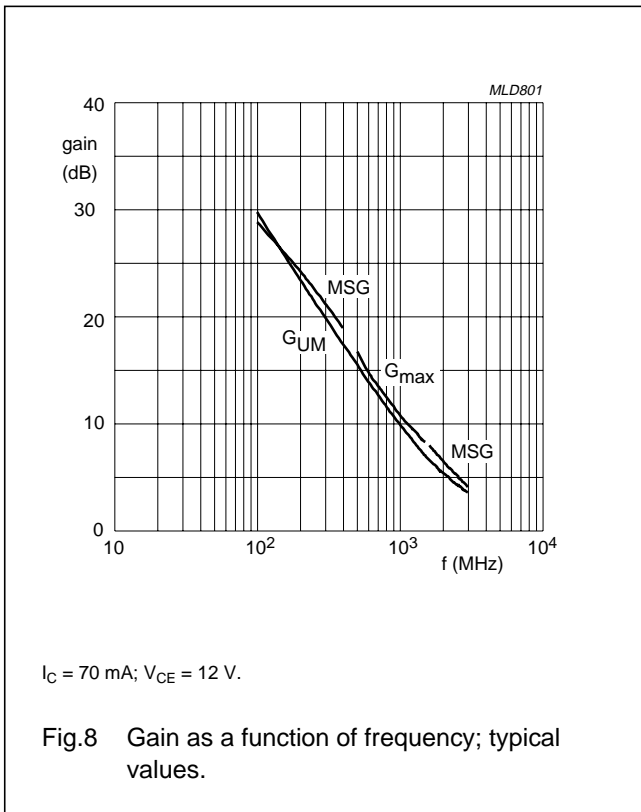
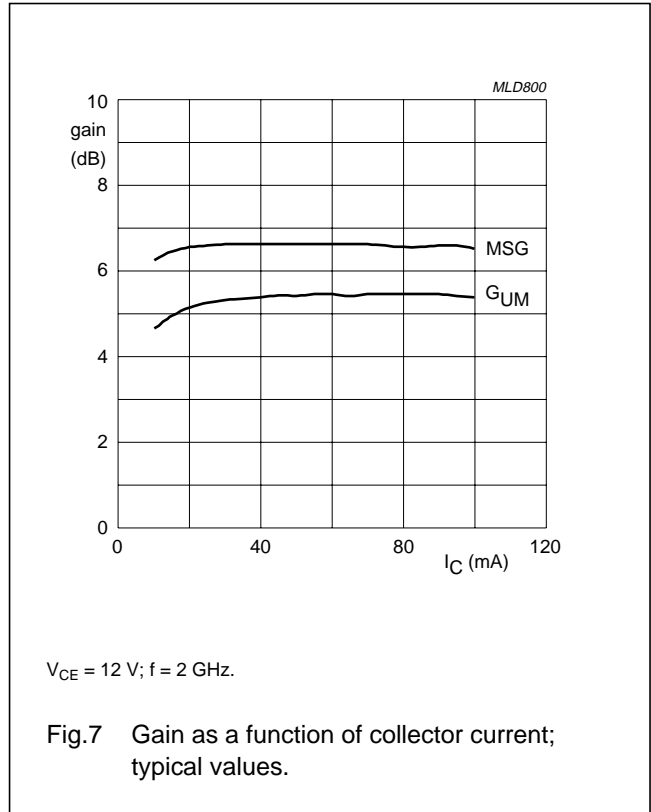
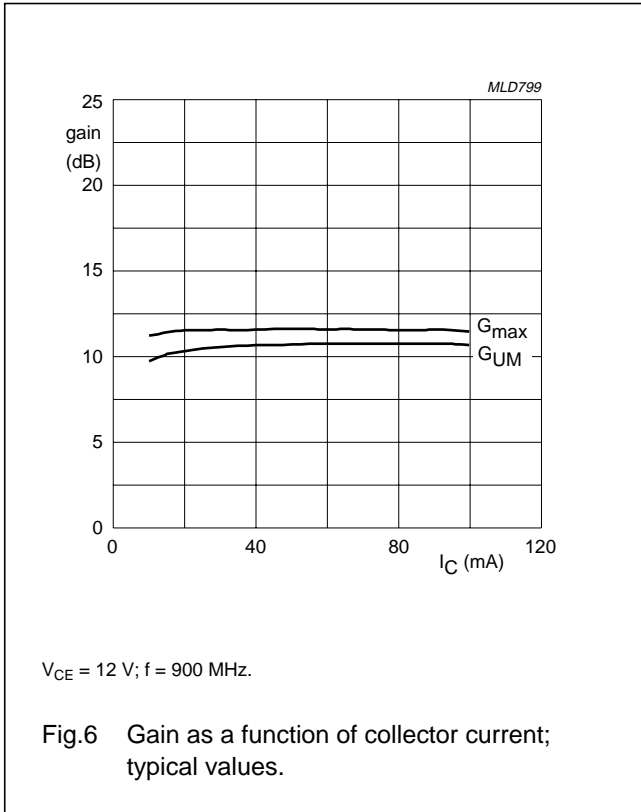
NPN 7 GHz wideband transistor

BFQ591



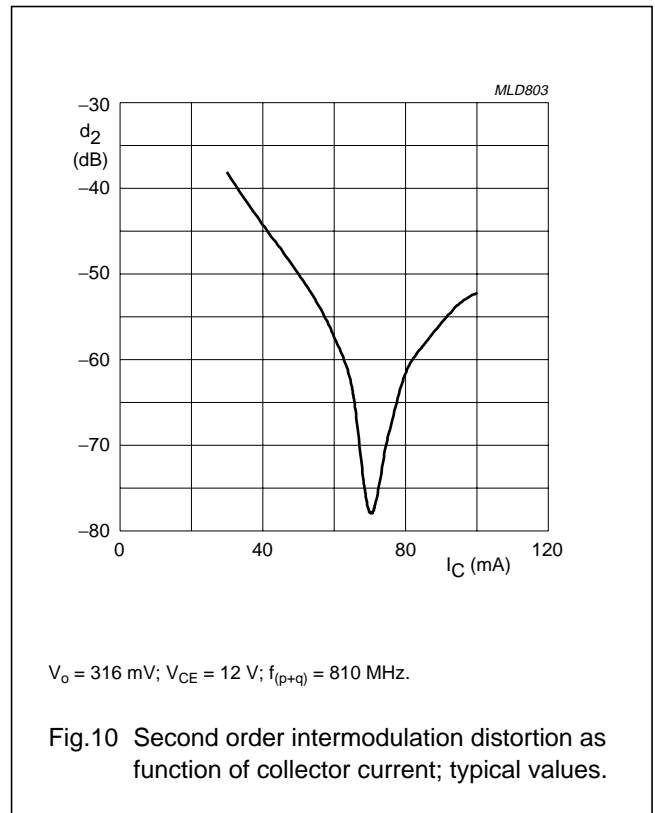
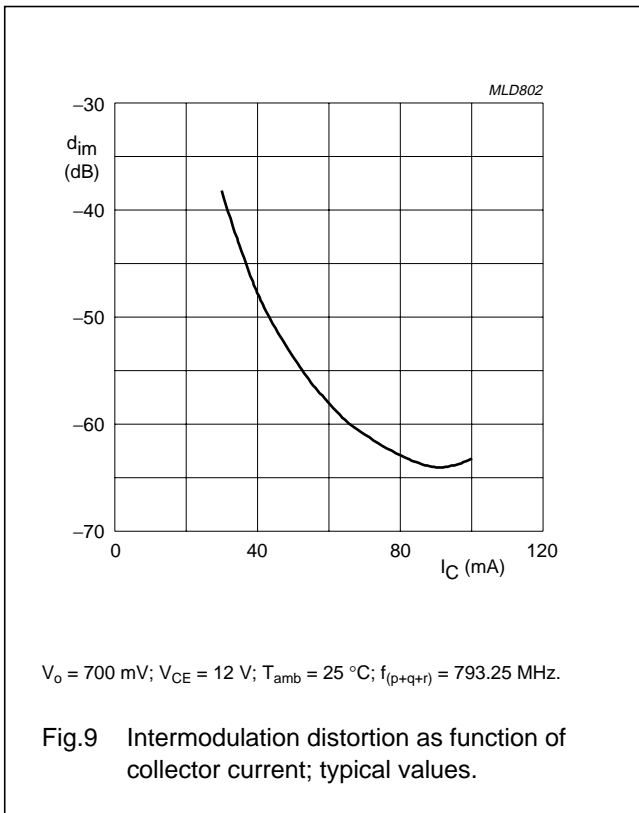
NPN 7 GHz wideband transistor

BFQ591



NPN 7 GHz wideband transistor

BFQ591



NPN 7 GHz wideband transistor

BFQ591

SPICE parameters for the BFQ591 die.

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.341	fA
2	BF	123.5	–
3	NF	.988	–
4	VAF	75.85	V
5	IKF	9.656	mA
6	ISE	232.2	fA
7	NE	2.134	–
8	BR	10.22	–
9	NR	1.016	–
10	VAR	1.992	V
11	IKR	294.1	mA
12	ISC	211.0	aA
13	NC	997.2	–
14	RB	5.00	Ω
15	IRB	1.000	μA
16	RBM	5.00	Ω
17	RE	1.275	Ω
18	RC	920.6	Ω
19 ⁽¹⁾	XTB	0.000	–
20 ⁽¹⁾	EG	1.110	eV
21 ⁽¹⁾	XTI	3.000	–
22	CJE	3.821	pF
23	VJE	600.0	mV
24	MJE	348.5	–
25	TF	13.60	ps
26	XTF	71.73	–
27	VTF	10.28	V
28	ITF	1.929	mA
29	PTF	0.000	deg
30	CJC	1.409	fF
31	VJC	219.4	mV
32	MJC	166.5	–
33	XCJ	2.340	–
34	TR	543.7	ps
35 ⁽¹⁾	CJS	0.000	F
36 ⁽¹⁾	VJS	750.0	mV
37 ⁽¹⁾	MJS	0.000	–
38	FC	733.2	–

Note

1. These parameters have not been extracted, the default values are shown.

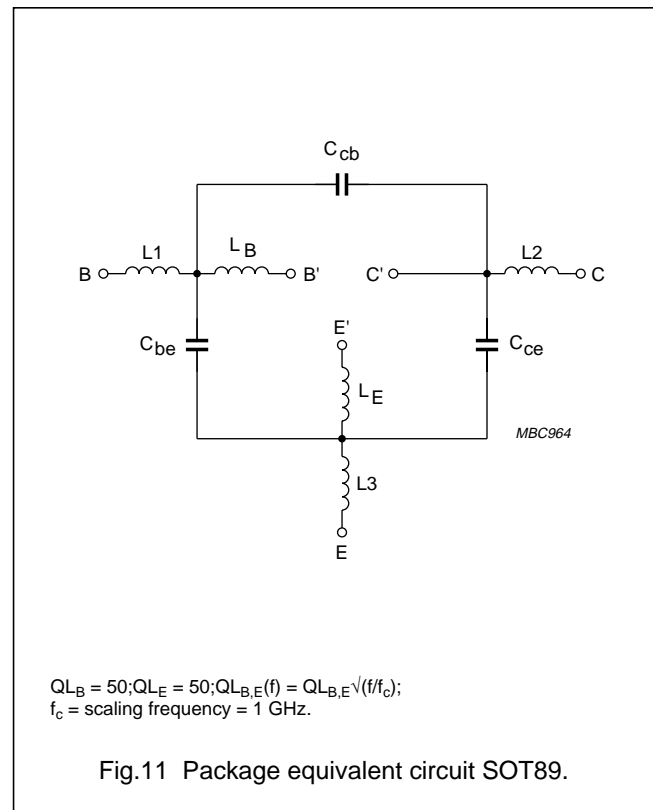


Fig.11 Package equivalent circuit SOT89.

List of components (see Fig.11)

DESIGNATION	VALUE	UNIT
C _{be}	16	fF
C _{cb}	150	fF
C _{ce}	150	fF
L1	1	nH
L2	0.01	nH
L3	1	nH
L _B	1.2	nH
L _E	1.2	nH

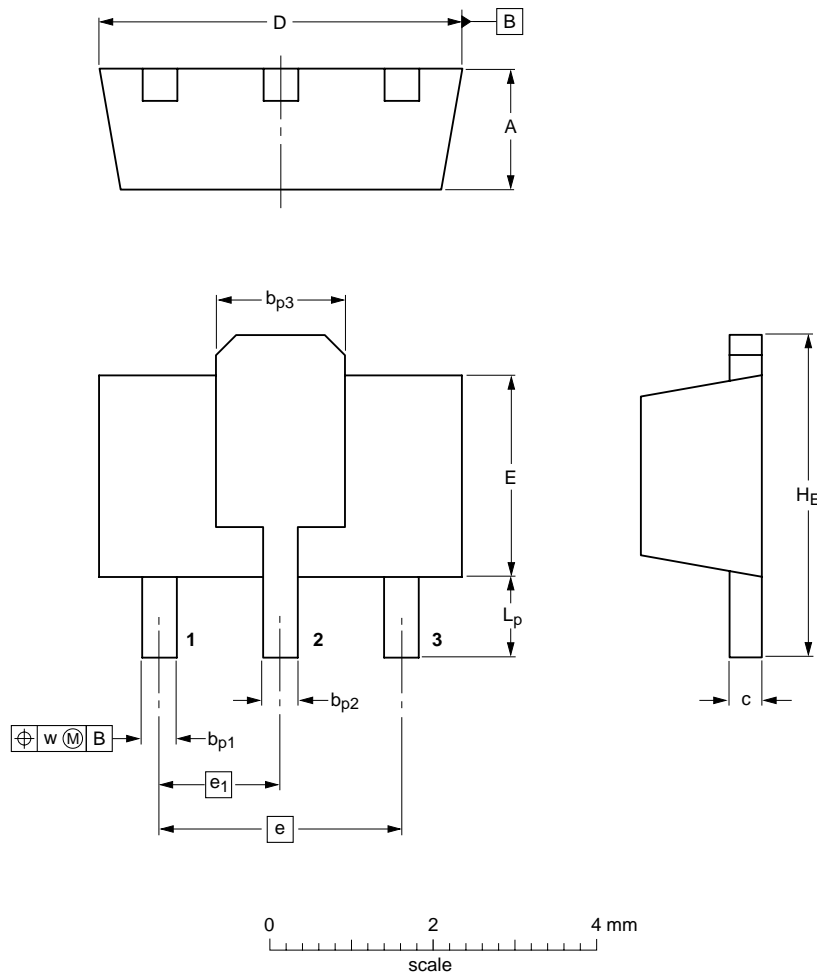
NPN 7 GHz wideband transistor

BFQ591

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		06-03-16 06-08-29

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Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFQ591_N_4	20071002	Product data sheet	-	BFQ591_3
Modifications:	• Fig. 1 and package outline updated			
BFQ591_3	20020204	Product specification	-	BFQ591_N_2
BFQ591_N_2 (9397 750 09252)	20020102	Preliminary specification	-	BFQ591_N_1
BFQ591_N_1 (9397 750 09013)	20011203	Preliminary specification	-	-

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